

NIS1050

Protection Interface Circuit for PMICs with Integrated OVP Control

The NIS1050 is a protection IC targeted at the latest generation of PMICs from the leading mobile phone and UMPC chipset vendors. It includes a highly stable low-current LDO and a low impedance power N-Channel MOSFET.

The LDO provides a low current, five volt supply to the PMIC, and the NFET is the external pass element for the OVIC circuit. These stages combine with the internal PMIC to protect the charging circuit from low-impedance overvoltage conditions that can occur from either the AC/DC or USB supply.

The NIS1050 is available in the low-profile 6-lead 2x2mm WDFN6 surface mount package.

Features

- Lower Power Dissipation and Higher Efficiency vs. Zener Shunt Regulator
- LDO Highly Stable across Temperature, Operates Without Bypass Capacitors
- Wide 3-30 V Power Supply Voltage Input Range
- Low-Profile (0.75mm) 6-Lead 2x2mm WDFN6 Package
- This is a Pb-Free Device

Typical Applications

- Power Interface for New Generation PMICs from Leading Mobile Phone and UMPC Chipset Vendors



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WDFN6, 2x2
CASE 506AN

MARKING DIAGRAMS



PM = Specific Device Code
M = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
NIS1050MNTBG	WDFN6 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

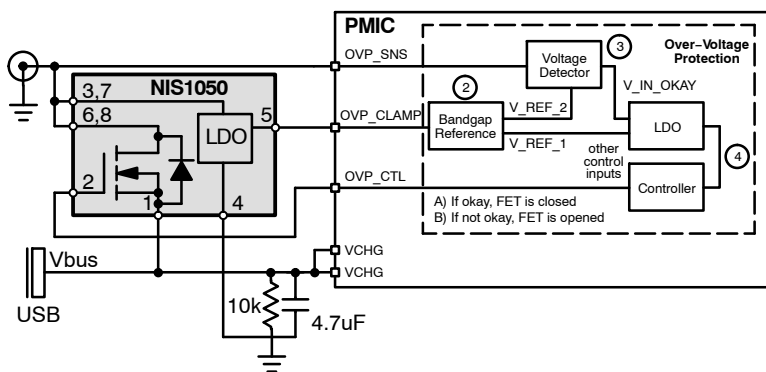


Figure 1. Typical Application

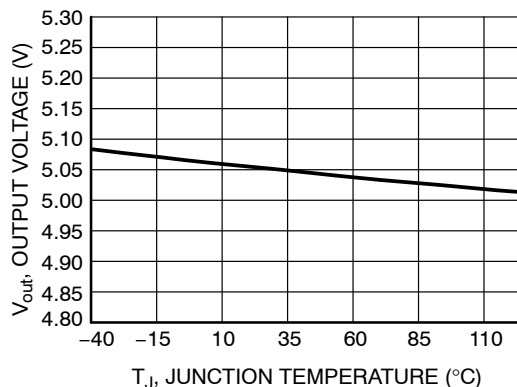


Figure 2. Output Voltage Variation with Temperature

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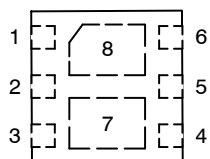


Figure 3. Pin Assignment

Table 1. FUNCTIONAL PIN DESCRIPTION

Pin	Function	Description
1	Source	This is the source of the power FET and connects to the PMIC pin of the same name.
2	Gate	This pin is the gate of the FET switch.
3, 7	V _{in}	Positive input voltage to the device.
4	Ground	Negative input voltage to the device. This is used as the internal reference for the IC.
5	V _{out}	This is the output of the internal LDO. It passes the input voltage through to the output and clamps that voltage if it exceeds the regulation limit.
6, 8	Drain	Positive input voltage to the device.

Table 2. MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Input Voltage, Operating, Steady-State (OVP_sense to Gnd)	V _{in}	-0.3 to 30	V
Gate-to-Source Voltage	V _{GS}	±8	V
Drain Current, Peak (10 μs pulse)	I _{Dpk}	20	A
Drain Current, Continuous (Note 1, Steady-State) T _A = 25°C T _A = 85°C	I _D	3.7 2.7	A
Total Power Dissipation @ T _A = 25°C (Note 1, 2)	P _{max}	750	mW
Operating Temperature Range	T _J	-40 to 125	°C
Non-operating Temperature Range	T _J	-55 to 150	°C
Maximum Lead Temperature for Soldering Purposes	T _L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface Mounted on FR4 Board using the minimum recommended pad size of 30 mm², 2 oz Cu.
2. Dual die operation (equally-heated).

Table 3. THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
SINGLE DIE OPERATION (SELF-HEATED)			
Junction-to-Ambient – Steady State (Note 3)	R _{θJA}	83	°C/W
Junction-to-Ambient – Steady State Min Pad (Note 4)	R _{θJA}	177	
Junction-to-Ambient – t ≤ 5 s (Note 3)	R _{θJA}	54	
DUAL DIE OPERATION (EQUALLY-HEATED)			
Junction-to-Ambient – Steady State (Note 3)	R _{θJA}	58	°C/W
Junction-to-Ambient – Steady State Min Pad (Note 4)	R _{θJA}	133	
Junction-to-Ambient – t ≤ 5 s (Note 3)	R _{θJA}	40	

3. Surface Mounted on FR4 Board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
4. Surface Mounted on FR4 Board using the minimum recommended pad size (30 mm², 2 oz Cu).

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Table 4. ELECTRICAL CHARACTERISTICS (Unless otherwise noted: V_{CC} (OVP_sense) = 5.0 V, T_J = 25°C)

Characteristics	Symbol	Min	Typ	Max	Unit
POWER FET					
Zero Gate Voltage Drain Current ($V_{DS} = 24 V_{dc}$, $V_{GS} = 0 V$) $T_J = 85^\circ C$	I_{DSS}			1.0 10	μA
Gate-to-Source Leakage Current ($V_{DS} = 0 V$, $V_{GS} = \pm 8 V$)	I_{GSS}			100	nA
Gate Threshold Voltage ($V_{GS} = V_{DS}$, $I_D = 250 \mu A$)	$V_{GS(th)}$	0.4	0.7	1.0	V
Negative Gate Threshold Temperature Coefficient	$V_{GS(th)}/T_J$		2.8		mV/°C
Drain-to-Source On-Resistance (Note 5) $V_{GS} = 4.5 V$, $I_D = 2.0 A$ $V_{GS} = 2.5 V$, $I_D = 2.0 A$	$R_{DS(on)}$		47 56	70 90	m Ω
Forward Transconductance ($V_{DS} = 5 V$, $I_D = 2.0 A$)	g_{FS}		4.5		S
Input Capacitance ($V_{DS} = 15 V_{dc}$, $V_{GS} = 0 V_{dc}$, $f = 1 MHz$)	C_{ISS}		427		pF
Output Capacitance ($V_{DS} = 15 V_{dc}$, $V_{GS} = 0 V_{dc}$, $f = 1 MHz$)	C_{OSS}		51		pF
Reverse Transfer Capacitance ($V_{DS} = 15 V_{dc}$, $V_{GS} = 0 V_{dc}$, $f = 1 MHz$)	C_{RSS}		32		pF
LDO (Unless otherwise noted, $T_J = 25^\circ C$, $V_{in} = 5.0 V$)					
Regulated Output Voltage ($V_{CC} = 5.5 V$ $I_o = 1 mA$)	V_{out}	4.6	5.0	5.3	V
Response to Input Transient (V_{in} 0 to 30 volts, $<1 \mu s$ rise time, 5.0 k Ω resistive load, Note 6) Time for signal above 5.5 volts Peak Voltage	t_{pulse} V_{pk}			5.0 9.0	μs V
Headroom ($V_{in} - V_{out}$, $I_{out} = 1.2 mA$, $V_{in} = 4.6 V$)	V_{head}			150	mV
Headroom ($V_{in} - V_{out}$, $I_{out} = 10 mA$, $V_{in} = 4.8 V$, $T_J = -40$ to $125^\circ C$)	V_{head}			1000	mV
TOTAL DEVICE					
Input Bias Current	I_{bias}		110	850	μA
Minimum Operating Voltage	V_{in-min}			3.0	V

5. Pulse test: Pulse width 300 μs , duty cycle 2%.

6. Guaranteed by design.

TYPICAL PERFORMANCE CURVES

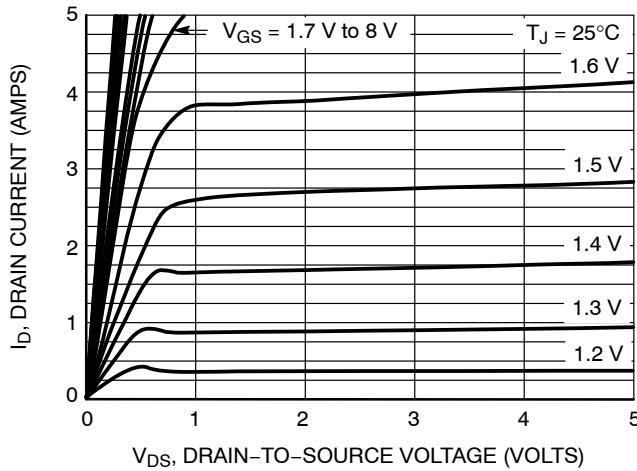


Figure 4. On-Region Characteristics

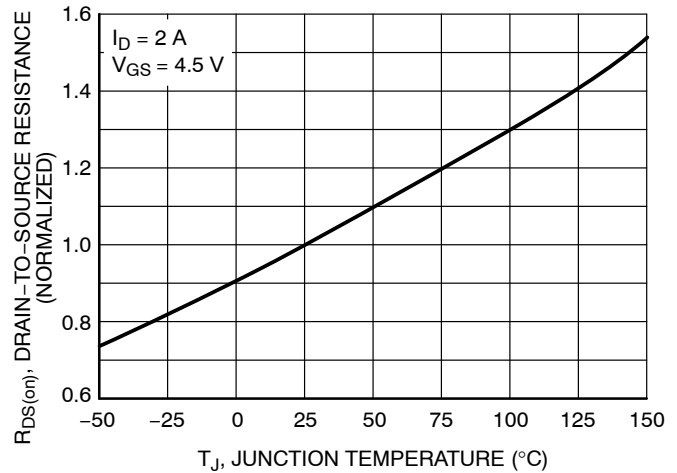


Figure 5. On-Resistance Variation with Temperature

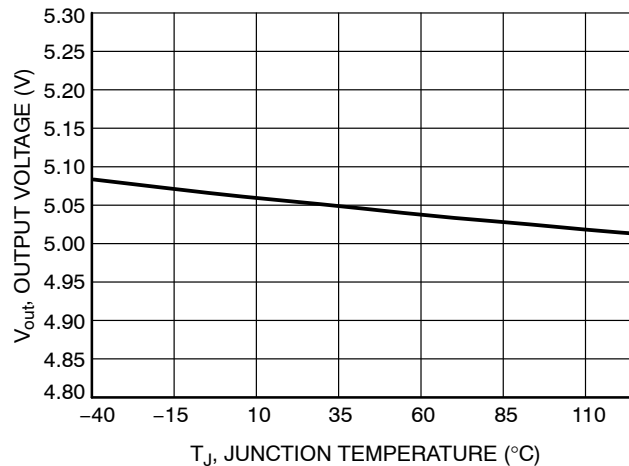


Figure 6. Output Voltage Variation with Temperature

Mounting Considerations

The LDO and MOSFET are both attached to thermal pads to provide a low impedance path for the heat generated in these devices. Both of these pads should have a solid connection to as much board copper area as possible in order to maintain a low operating temperature. The main purpose of both of these pads is for thermal connections, not electrical connections.

Pad 7 is the input voltage for the LDO. It is electrically connected to the Vcc pin. This connection is optional and will have a negligible difference in the electrical performance of the chip due to the current into the LDO.

Pad 8 is the drain of the power MOSFET. This pad will also have a low electrical impedance. Either pad 8, pad 6 or both may be used for electrical connections. The total

impedance of the FET will not vary significantly since pad 6 is part of the lead-frame and therefore connected to pad 8 by a metal path on the lead frame. The majority of the package impedance comes from the resistance between the source and pin 1, since this is connected by bond wires.

Bypass Capacitors

The LDO has been designed to operate in a stable mode without bypass capacitors; however, it is recommended to use a low ESR capacitor if fast, ac transients or other switching type currents will be present. Typically, a value of 1 to 10 nF is adequate for an output bypass capacitor. A 1 nF capacitor may be added to the input if the input source is noisy or if it has a high ac impedance due to long trace lengths.

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